

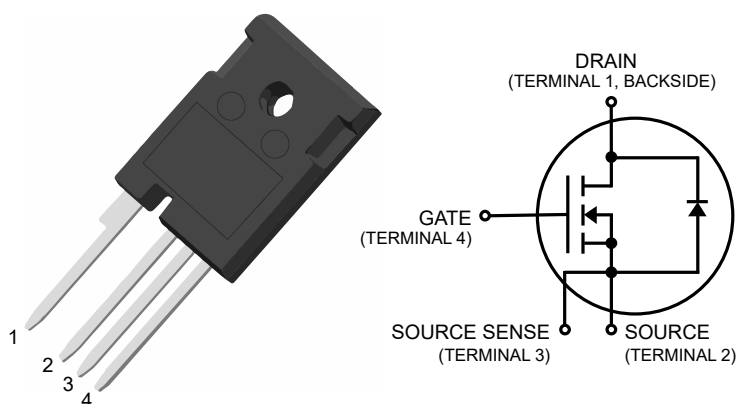
3300V, 80 mΩ N-Channel mSiC™ MOSFET

MSC080SMA330B4N



Product Overview

3300V, 80 mΩ typical at $V_{GS} = 20V$, 90 mΩ typical at $V_{GS} = 18V$, Silicon Carbide (SiC) N-Channel MOSFET, TO-247 notched 4-lead with a source sense.



Features

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_{J(max)} = 150\text{ }^{\circ}\text{C}$
- Fast and reliable body diode
- RoHS compliant

Benefits

- High efficiency to enable lighter and more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

Applications

- Photovoltaic (PV) inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- Hybrid Electric Vehicle (HEV) powertrain and Electric Vehicle (EV) charger
- Power supply and distribution

1. Device Specifications

This section shows the specifications of this device.

1.1. Absolute Maximum Ratings

The following table shows the absolute maximum ratings of this device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
V_{DSS}	Drain source voltage	3300	V
I_D	Continuous drain current at $T_C = 25\text{ }^{\circ}\text{C}$	43	A
	Continuous drain current at $T_C = 100\text{ }^{\circ}\text{C}$	27	
I_{DM}	Pulsed drain current ¹	107	
V_{GS}	Gate-source voltage	23 to -10	V
	Transient gate-source voltage	25 to -12	
P_D	Total power dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	439	W
	Linear derating factor	3.6	

Note:

1. Repetitive rating; pulse width and case temperature are limited by the maximum junction temperature.

The following table shows the thermal and mechanical characteristics of this device.

Table 1-2. Thermal and Mechanical Characteristics

Symbol	Characteristic/Test Conditions	Min.	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance	—	0.22	0.28	$^{\circ}\text{C}/\text{W}$
T_J	Operating junction temperature	-55	—	150	$^{\circ}\text{C}$
T_{STG}	Storage temperature	-55	—	150	
T_L	Lead temperature for 10 seconds	—	—	300	$^{\circ}\text{C}$
τ_M	Mounting torque, M3 screw for heat sink attachment (requires 1, not included)	—	0.8	—	N·m
Wt	Package weight	—	6.2	—	g

ESD practices should comply with JESD-625.

1.2. Electrical Performance

The following table shows the static characteristics of this device. $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 1-3. Static Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{V}, I_D = 100\text{ }\mu\text{A}$	3300	—	—	V
$R_{DS(on)}$	Drain-source on resistance ¹	$V_{GS} = 20\text{V}, I_D = 30\text{A}$	—	85	106	$\text{m}\Omega$
		$V_{GS} = 18\text{V}, I_D = 30\text{A}$	—	90	—	
$V_{GS(th)}$	Gate-source threshold voltage	$V_{GS} = V_{DS}, I_D = 3\text{ mA}$	1.9	3.0	5.0	V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 3300\text{V}, V_{GS} = 0\text{V}$	—	0.30	35	μA
		$V_{DS} = 3300\text{V}, V_{GS} = 0\text{V}, T_J = 150\text{ }^{\circ}\text{C}$	—	3.5	—	
I_{GSS}	Gate-source leakage current	$V_{GS} = 20\text{V}/-10\text{V}$	—	—	± 100	nA

Note:

1. Pulse test: pulse width < 380 μ s, duty cycle < 2%.

The following table shows the dynamic characteristics of this device. $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified. The dynamic characteristics are characterized, not 100% tested, at the recommended operating $V_{GS} = 20\text{V}/-5\text{V}$.

Table 1-4. Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{V}$, $V_{DD} = 2400\text{V}$, $V_{AC} = 25\text{ mV}$, $f = 200\text{ kHz}$	—	3462	—	pF
C_{rss}	Reverse transfer capacitance		—	4.0	—	
C_{oss}	Output capacitance		—	77	—	
Q_G	Total gate charge	$V_{GS} = -5\text{V}/20\text{V}$, $V_{DD} = 2650\text{V}$, $I_D = 30\text{A}$	—	161	—	nC
Q_{GS}	Gate-source charge		—	55	—	
Q_{GD}	Gate-drain charge		—	51	—	
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 2310\text{V}$, $V_{GS} = -5\text{V}/20\text{V}$, $I_D = 20\text{A}$, $R_{G(ext)} = 8\Omega$, Freewheeling diode = MSC080SMA330B4N ($V_{GS} = -5\text{V}$); reference Figure 1-19	—	34	—	ns
t_r	Voltage rise time		—	25	—	
$t_{d(off)}$	Turn-off delay time		—	50	—	
t_f	Voltage fall time		—	32	—	
E_{on}	Turn-on switching energy		—	1590	—	μ J
E_{off}	Turn-off switching energy		—	450	—	
ESR	Gate equivalent series resistance	$f = 1\text{ MHz}$, 25 mV , drain short	—	3.7	—	Ω

The following table shows the body diode characteristics of this device. $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified. The body diode reverse recovery is characterized, not 100% tested.

Table 1-5. Body Diode Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	$I_{SD} = 30\text{A}$, $V_{GS} = 0\text{V}$	—	4.0	—	V
		$I_{SD} = 30\text{A}$, $V_{GS} = -5\text{V}$	—	4.2	5.0	
t_{rr}	Reverse recovery time	$I_{SD} = 20\text{A}$, $V_{GS} = -5\text{V}$, Drive $R_G = 8\Omega$, $V_{DD} = 2310\text{V}$, $dI/dt = -3760\text{ A}/\mu\text{s}$	—	35	—	ns
Q_{rr}	Reverse recovery charge		—	818	—	nC
I_{RRM}	Reverse recovery current		—	41	—	A

1.3. Typical Performance Curves

Data for performance curves are characterized, not 100% tested.

Figure 1-1. Drain Current vs. V_{DS} at T_J

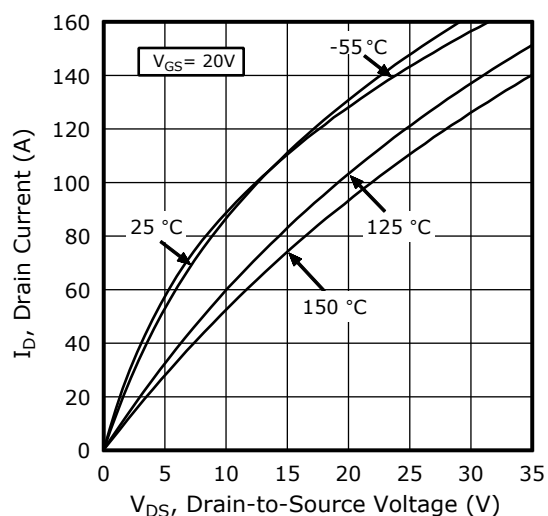


Figure 1-2. Drain Current vs. V_{DS} at V_{GS}

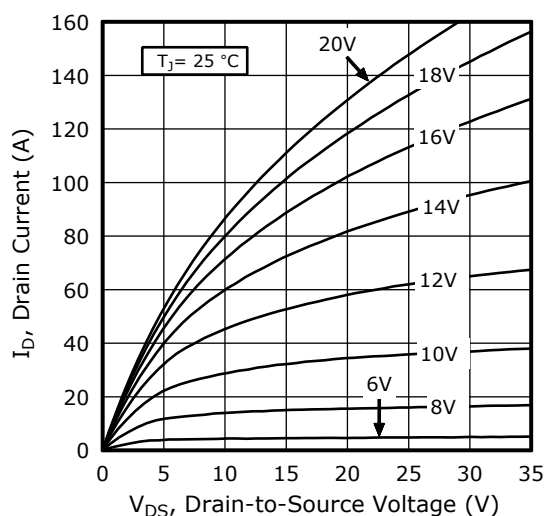


Figure 1-3. Drain Current vs. V_{DS} at V_{GS}

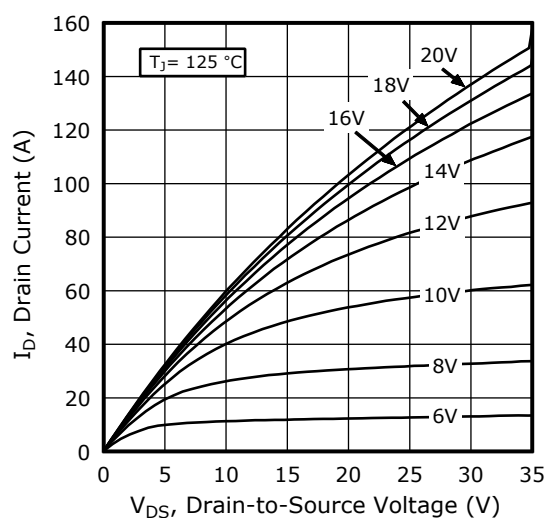


Figure 1-4. Drain Current vs. V_{DS} at V_{GS}

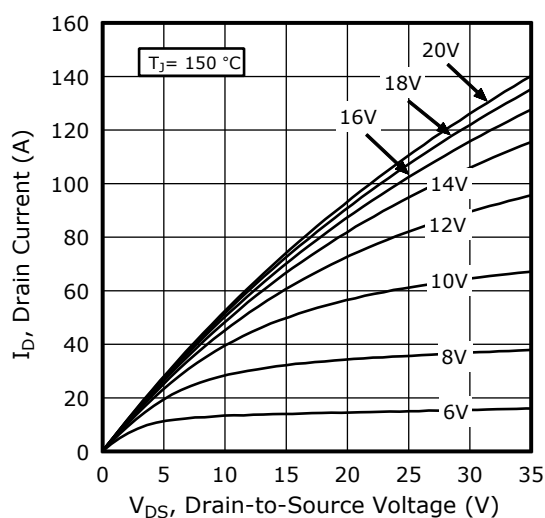


Figure 1-5. $R_{DS(on)}$ vs. Junction Temperature

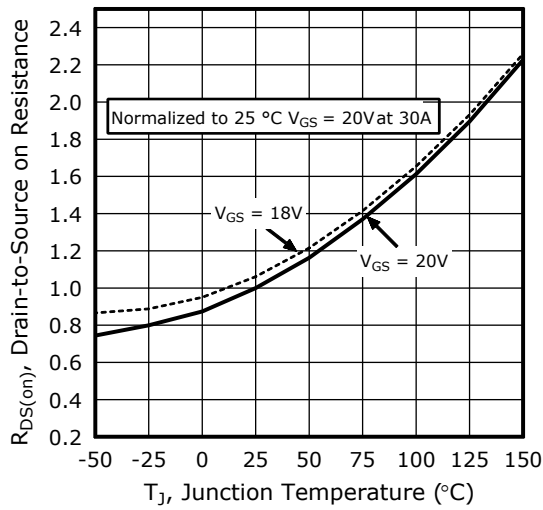


Figure 1-6. Gate Charge Characteristics

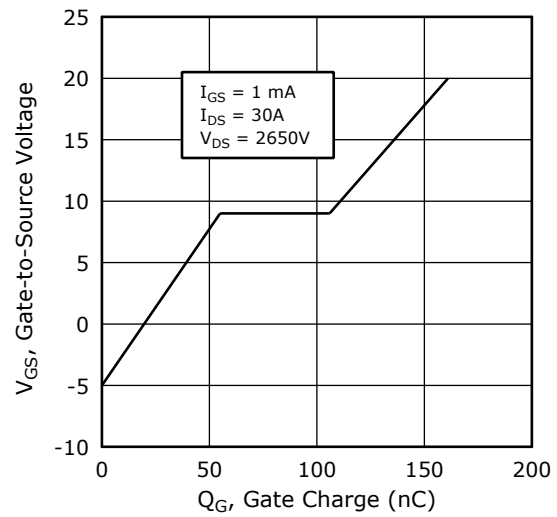


Figure 1-7. Capacitance vs. Drain-to-Source Voltage

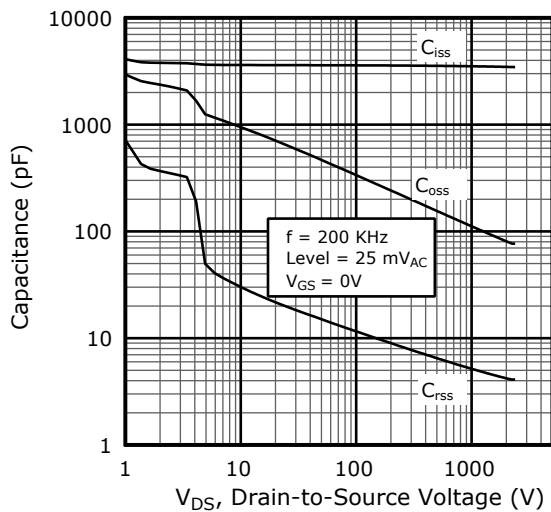


Figure 1-8. Output Charge vs. Drain-to-Source Voltage

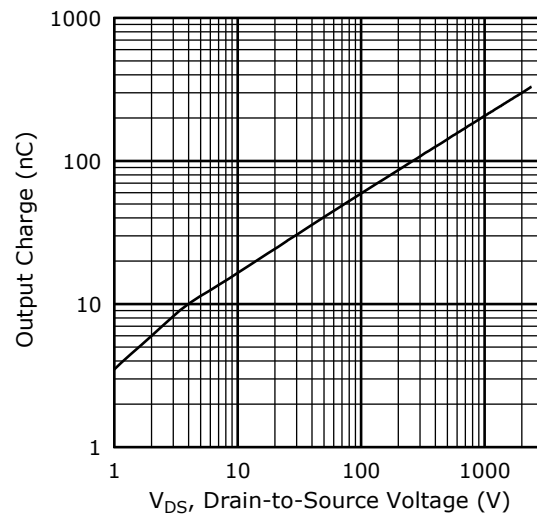


Figure 1-9. Output Stored Energy vs. V_{DS}

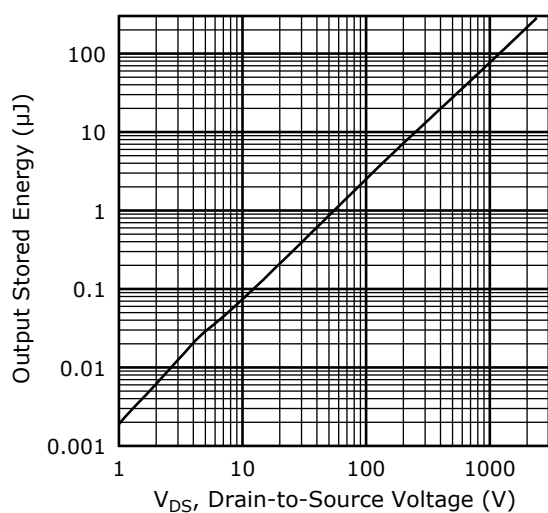


Figure 1-10. I_D vs. V_{DS} 3rd Quadrant Conduction

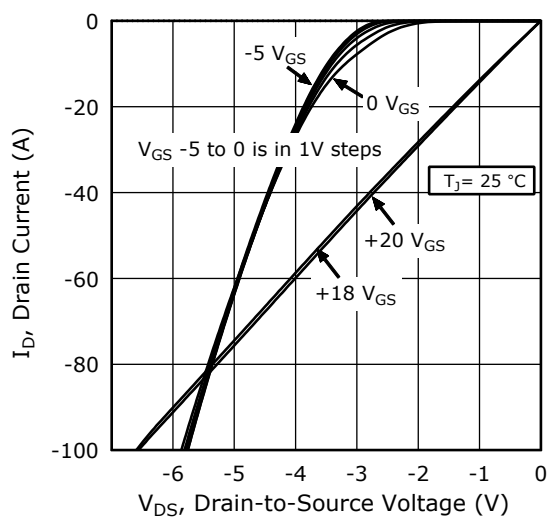


Figure 1-11. I_D vs. V_{DS} 3rd Quadrant Conduction

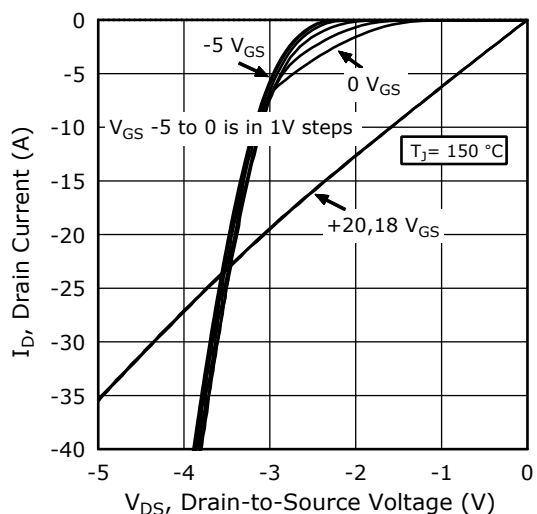


Figure 1-12. Switching Energy E_{on} vs. V_{DS} & I_D

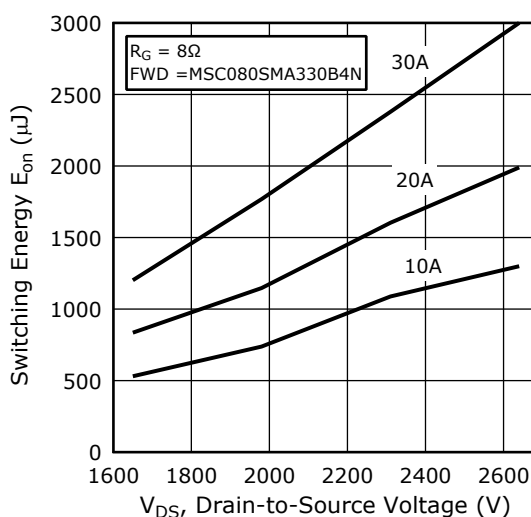


Figure 1-13. Switching Energy E_{off} vs. V_{DS} & I_D

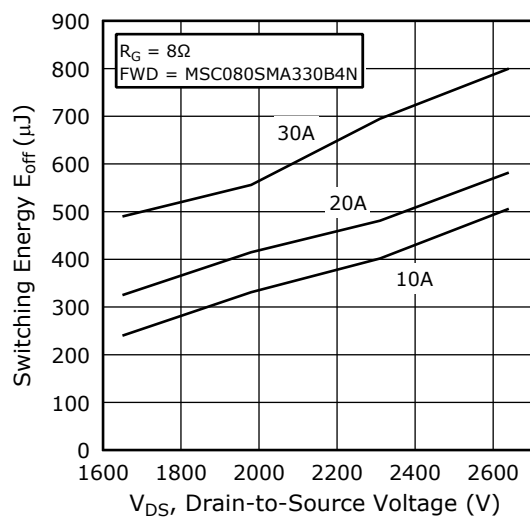


Figure 1-14. Switching Energy vs. R_G

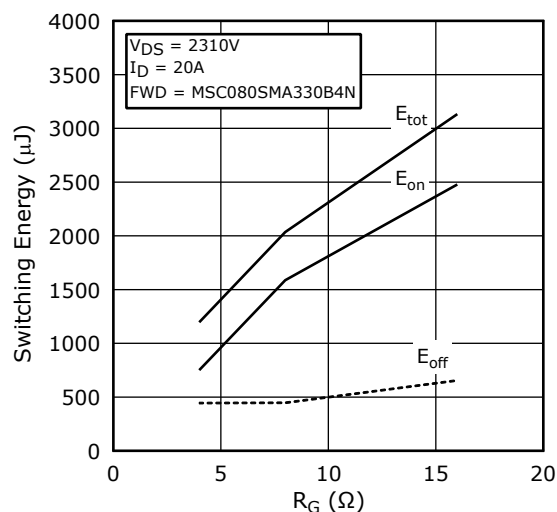


Figure 1-15. Switching Energy vs. Junction Temperature

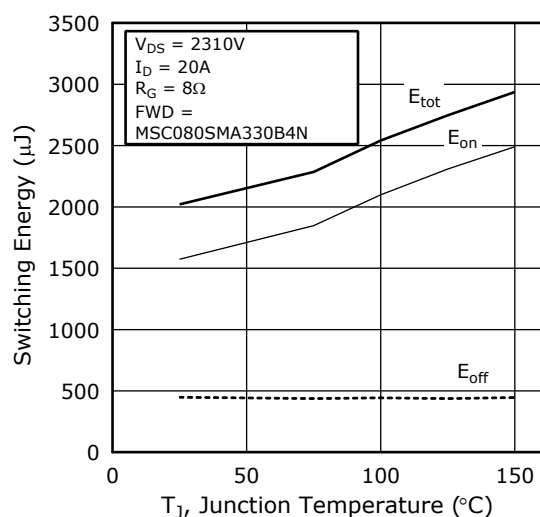


Figure 1-16. Threshold Voltage vs. Junction Temperature

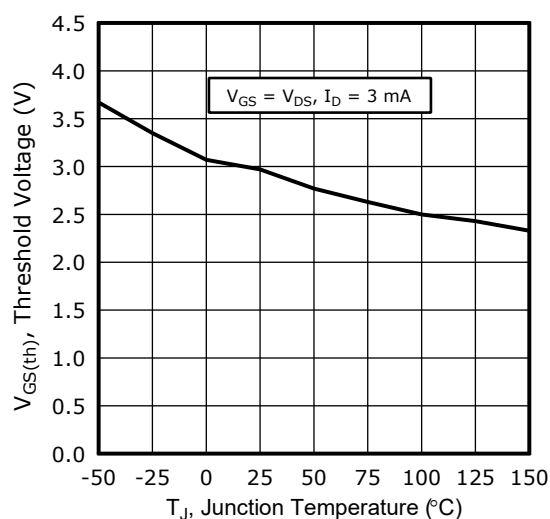


Figure 1-17. Forward Safe Operating Area

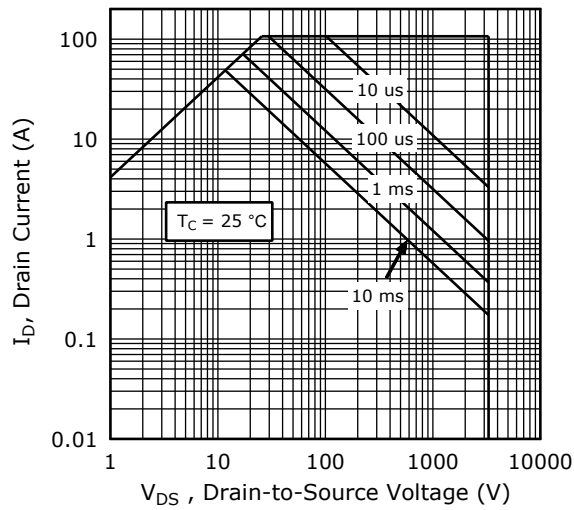
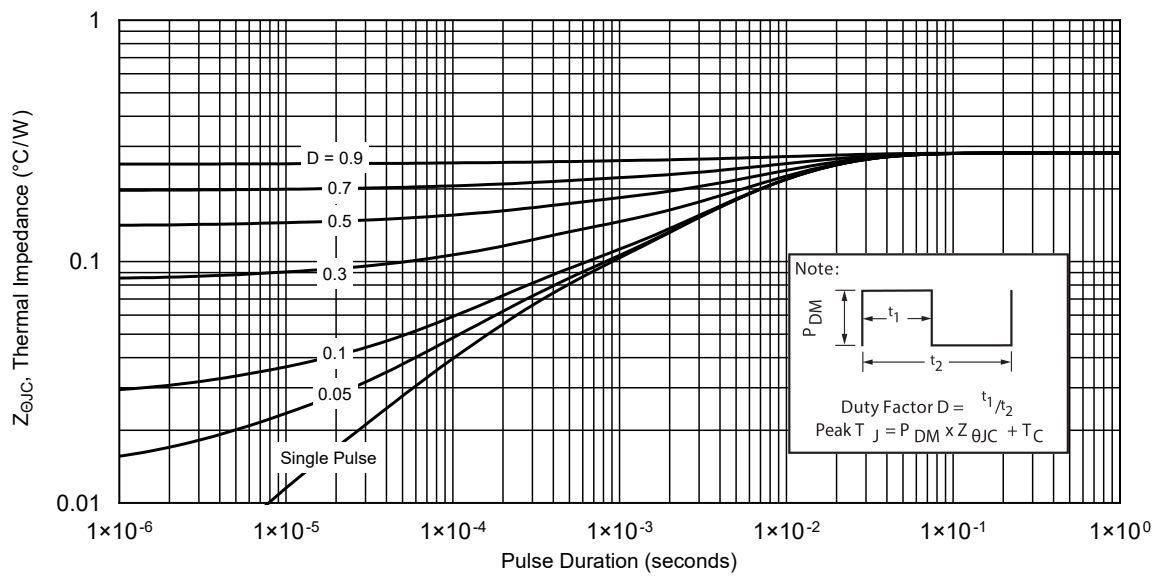
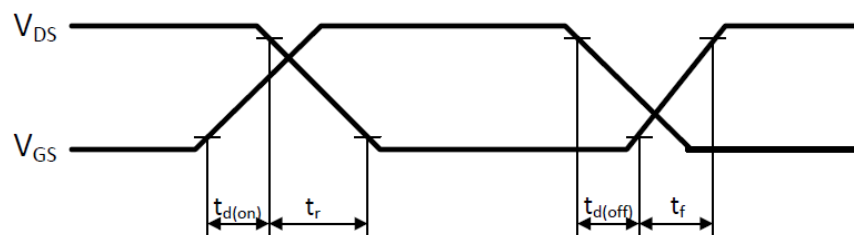


Figure 1-18. Maximum Transient Thermal Impedance



The following figure shows the switching waveform diagram of this device.

Figure 1-19. Switching Waveform



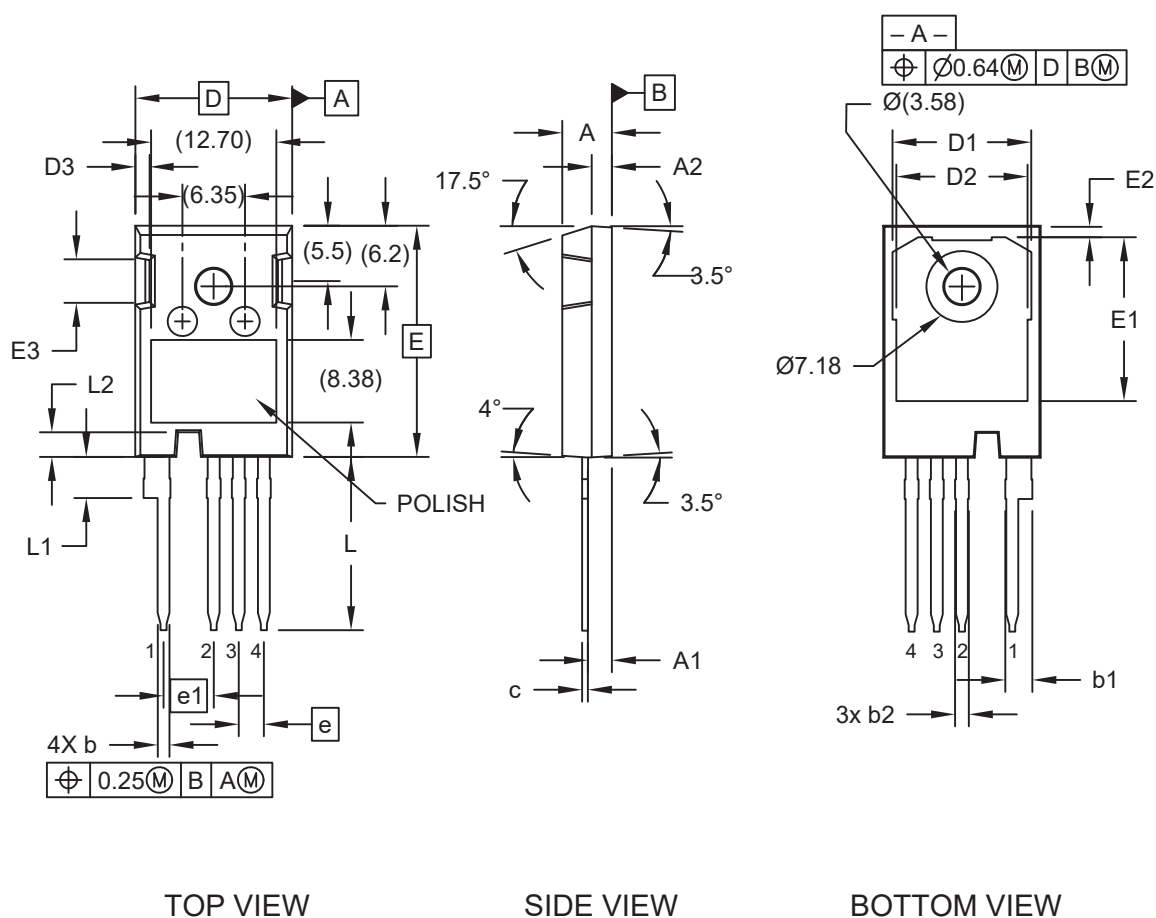
2. Package Specification

This section shows the package specification of this device.

2.1. Package Outline Drawing

The following figure illustrates the TO-247 notched-4L package outline of this device.

Figure 2-1. Package Outline Drawing



The following table shows the TO-247 notched-4L dimensions and should be used in conjunction with the package outline drawing.

Table 2-1. TO-247 Notched-4L Dimensions

Symbol	Description	Min. (mm)	Nom. (mm)	Max. (mm)
N	Number of terminals	4		
e	Pitch	2.54 BSC		
e1		5.08 BSC		
A	Overall height	4.83	5.02	5.21
A1	Standoff	2.29	2.41	2.54
A2	Exposed pad thickness	1.91	2.03	2.16
c	Terminal thickness	0.55	0.60	0.68
D	Overall length	15.75	15.94	16.13

Table 2-1. TO-247 Notched-4L Dimensions (continued)

Symbol	Description	Min. (mm)	Nom. (mm)	Max. (mm)
D1	Exposed pad length	13.10	13.62	14.15
D2		12.38	12.90	13.43
D3	Cutout length	1.00	1.45	1.90
E	Overall width	23.30	23.45	23.60
E1	Exposed pad width	16.25	16.95	17.65
E2	Exposed pad gap to edge	0.95	1.10	1.25
E3	Cutout width	3.68	4.39	5.10
b	Terminal width	1.07	1.20	1.33
b1	Terminal shoulder width (X1)	2.39	2.66	2.94
b2	Terminal shoulder width (X3)	1.07	1.33	1.60
L	Terminal length	17.31	17.56	17.82
L1	Terminal shoulder length	3.97	4.17	4.37
L2	Notch depth	2.35	2.50	2.65

Note:

Dimensioning and tolerancing per ASME Y14.5M.

- BSC: Basic dimension. Theoretically exact value shown without tolerances.

3. Revision History

The revision history describes the changes that were implemented in the document. The changes are listed by revision, starting with the most current publication.

Table 3-1. Revision History

Revision	Date	Description
A	04/2025	Initial revision

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